

2SB552

SILICON PNP TRIPLE DIFFUSED TYPE

HIGH POWER AMPLIFIER APPLICATIONS.
HIGH POWER SWITCHING APPLICATIONS.
DC-DC CONVERTER APPLICATIONS.
REGULATOR APPLICATIONS.

FEATURES:

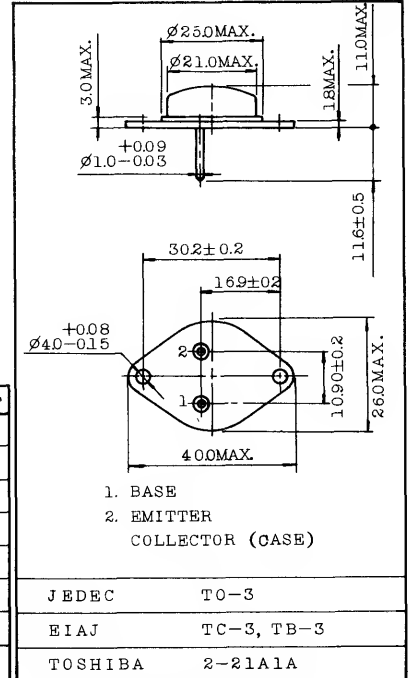
- High Collector Power Dissipation : $P_C=150W$ ($T_c=25^\circ C$)
- High Collector Current : $I_C=-15A$
- High Voltage : $V_{CE0}=-180V$
- Complementary to 2SD552.

MAXIMUM RATINGS ($T_a=25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CB0}	-220	V
Collector-Emitter Voltage	V_{CE0}	-180	V
Emitter-Base Voltage	V_{EB0}	-5	V
Collector Current	I_C	-15	A
Base Current	I_B	-3	A
Collector Power Dissipation ($T_c=25^\circ C$)	P_C	150	W
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature Range	T_{stg}	-65~150	$^\circ C$

INDUSTRIAL APPLICATIONS

Unit in mm



Mounting Kit No. AC73

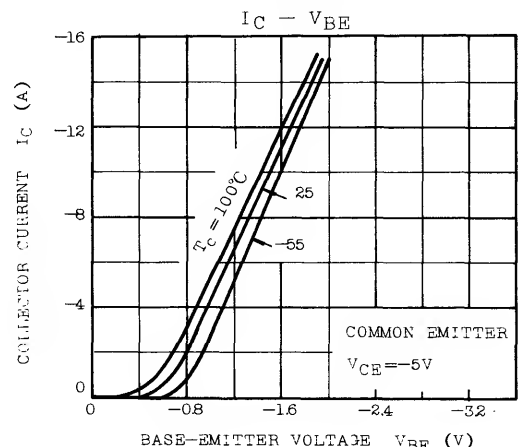
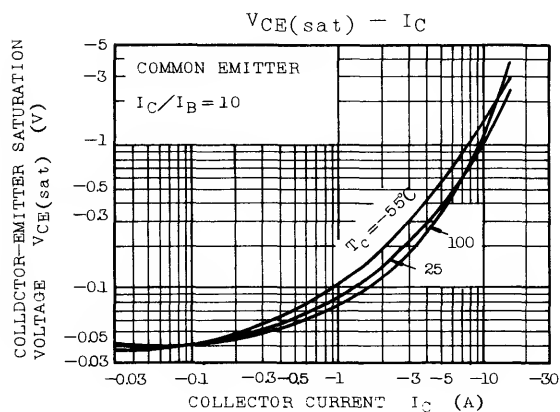
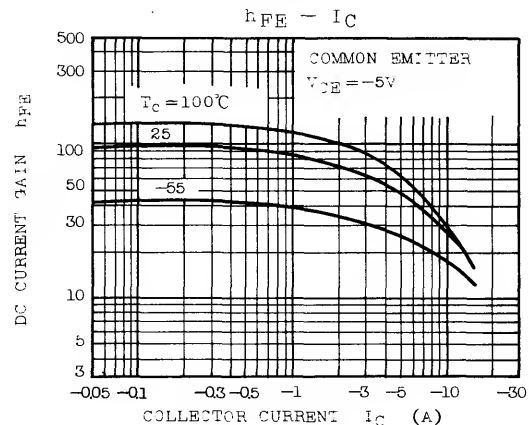
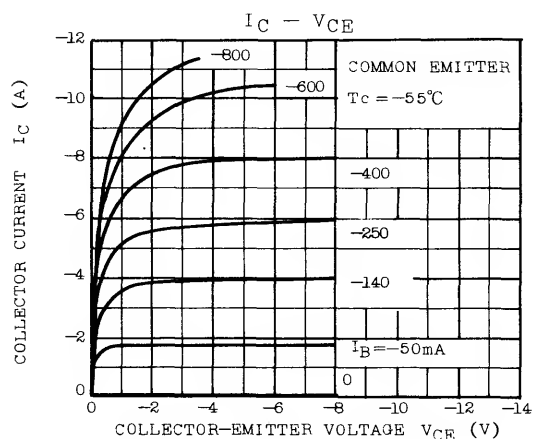
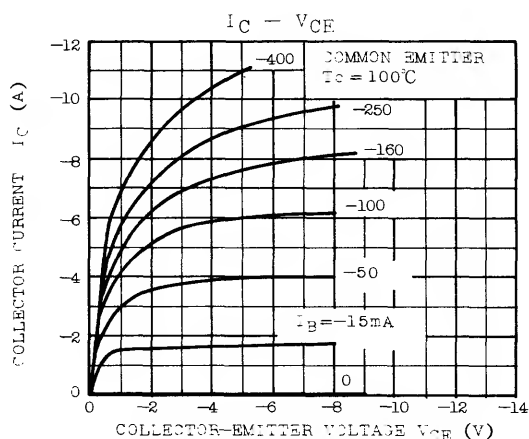
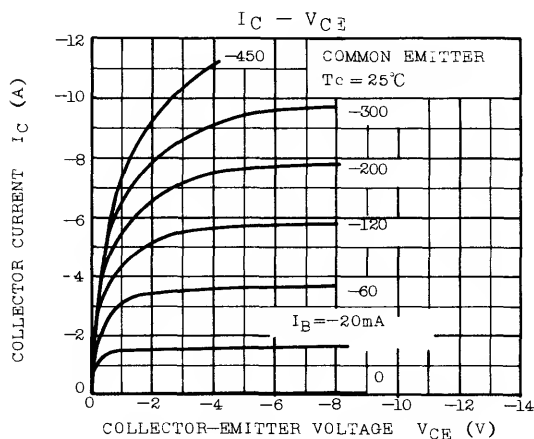
Weight : 12.9g

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ C$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CB0}	$V_{CB}=-150V, I_E=0$	-	-	-100	μA
Emitter Cut-off Current	I_{EB0}	$V_{EB}=-5V, I_C=0$	-	-	-1	mA
Collector-Emitter Breakdown Voltage	$V(BR)_{CE0}$	$I_C=-50mA, I_B=0$	-180	-	-	V
DC Current Gain	$h_{FE}(1)$ (Note)	$V_{CE}=-5V, I_C=-5A$	25	-	80	
	$h_{FE}(2)$	$V_{CE}=-5V, I_C=-15A$	10	15	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-10A, I_B=-1A$	-	-	-2.0	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=-10A, I_B=-1A$	-	-1.6	-2.5	V
Transition Frequency	f_T	$V_{CE}=-10V, I_C=-1A$	-	3.5	-	MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=-50V, I_E=0, f=1MHz$	-	300	-	pF
Switching Time	Turn-on Time	t_{on}	-	1	-	μs
	Storage Time	t_{stg}	-	4	-	
	Fall Time	t_f	-	0.5	-	

$V_{CC}=-125V$

Note : $h_{FE}(1)$ Classification BN : 25~50, R : 40~80



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